

## Topics

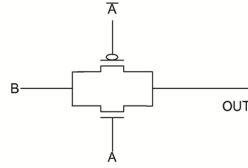
- Pass-transistor Logic
- Dynamic CMOS

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## Pass-Transistor Logic

- Transmission Gate



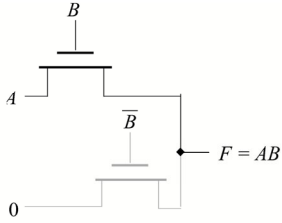
A	B	OUT
0	0	Z
0	1	Z
1	0	0
1	1	1

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## Pass-Transistor Logic

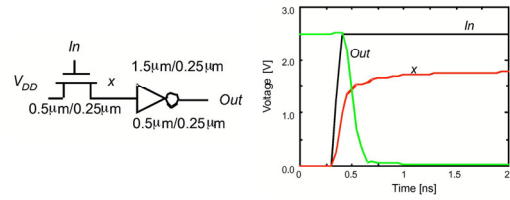
- Example: AND Gate



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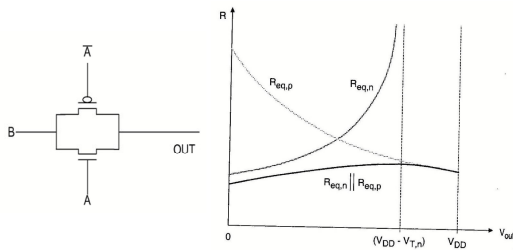
## NMOS-Only Logic



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## Resistance of Transmission Gate

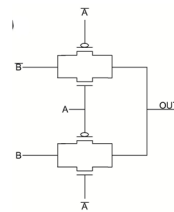


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## Pass-Transistor Logic

- XOR



A	B	OUT
0	0	0
0	1	1
1	0	1
1	1	0

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## Pass-Transistor Logic

- In many cases, uses fewer transistors
- Can be difficult to design
- Usually requires complemented versions of all signals
- Difficult to layout
- Transmission gate looks like a RC line
- Delay analysis is not as well defined in terms of sizing choices

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## Dynamic CMOS

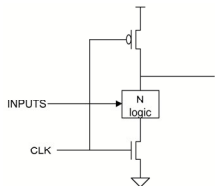
- In static circuits at every point in time (except when switching) the output is connected to either GND or VDD via a low resistance path.
  - fan-in of  $n$  requires  $2n$  transistors ( $n$  N-type and  $n$  P-type)
- Dynamic circuits rely on the temporary storage of signal values on the capacitance of high impedance nodes.
  - requires only  $n+2$  ( $n+1$  N-type and 1 P-type) transistors (can be further reduced to  $n+1$ )

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## Dynamic CMOS

- nMOS logic structure with pre-charged pullup

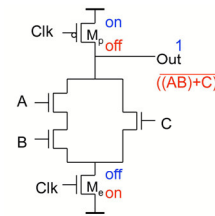


- Pre-charge to VDD when clock is low
- Evaluate when clock is high

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## Dynamic Gate



Two phase operation

- Precharge (CLK = 0)
- Evaluate (CLK = 1)

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## Conditions on Output

- Once the output of a dynamic gate is discharged, it cannot be charged again until the next pre-charge operation.
- Inputs to the gate can make at most one transition during evaluation.
- Output can be in the high impedance state during and after evaluation (PDN off), state is stored on  $C_L$

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## Properties of Dynamic Gates

- Logic function is implemented by the PDN only
  - number of transistors is  $N + 2$  (versus  $2N$  for static complementary CMOS)
- Full swing outputs ( $V_{OL} = \text{GND}$  and  $V_{OH} = V_{DD}$ )
- Sizing of the devices does not affect the logic levels (ratioless)

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## Properties of Dynamic Gates

- Faster switching speeds
  - reduced load capacitance due to smaller input capacitance ( $C_{in}$ )
  - reduced load capacitance due to smaller output loading ( $C_{out}$ )
  - Ideally, no  $I_{scr}$ , so all the current provided by PDN goes into discharging  $C_L$

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## Properties of Dynamic Gates

- Overall power dissipation usually higher than static CMOS (mainly due to clock)
  - no static current path exists between VDD and GND
  - no glitching (static CMOS has many glitches)
  - higher transition probabilities
  - extra load on Clk

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## Properties of Dynamic Gates

- PDN starts to work as soon as the input signals exceed  $V_{Tnr}$ 
  - low noise margin (NML)
- Needs a pre-charge/evaluate clock

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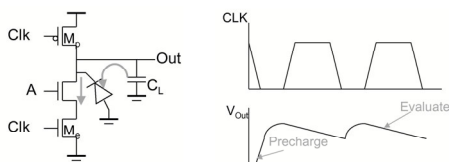
## Dynamic CMOS

- Advantages
  - Fewer transistors than CMOS
  - Smaller load capacitance - faster speed
- Disadvantages
  - Leakage
  - Charge sharing
  - Cannot be cascaded directly
  - Only 0→1 transitions allowed at inputs, thus cannot be connected to static gate directly

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## Issues in Dynamic Design 1: Charge Leakage



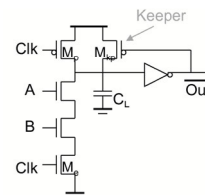
Leakage sources

Dominant component is sub-threshold current

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## Solution to Charge Leakage

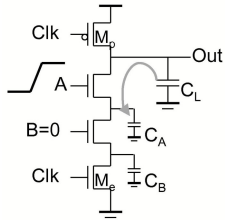


- Increase size of inverter to increase capacitance

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## Issues in Dynamic Design 2: Charge Sharing



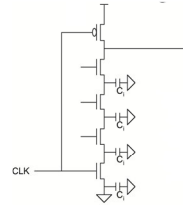
Charge stored originally on  $C_L$  is redistributed (shared) over  $C_L$  and  $C_A$  leading to reduced robustness

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## Dynamic CMOS

### • Charge Sharing

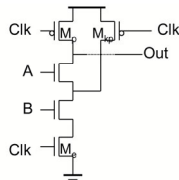


- Assume that the internal capacitances have been discharged
- In the pre-charge phase, the output capacitance gets charged
- During evaluation, if all the inputs are high except the bottom one, the output capacitance gets distributed to the internal capacitance
- The output voltage will drop to  $V_{DD} \frac{C_o}{C_o + 2C_i}$
- This could be low enough to trigger the inverter, causing a wrong value on the output

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## Solution to Charge Sharing



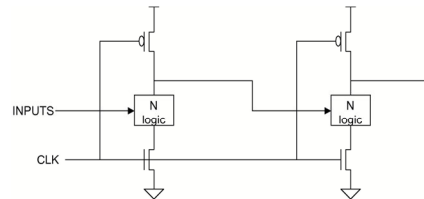
Pre-charge internal nodes using a clock driven transistor (at the cost of increased area and power)

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## Dynamic CMOS

### • Cascade problem

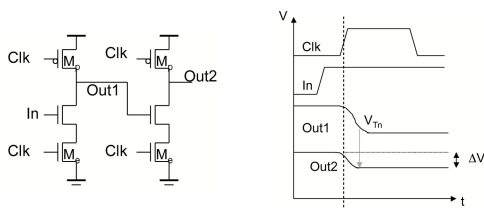


Since the evaluation from the first stage takes some time, the second stage will start evaluating with the pre-charged internal value rather than the inputs

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## Cascading Dynamic Gates



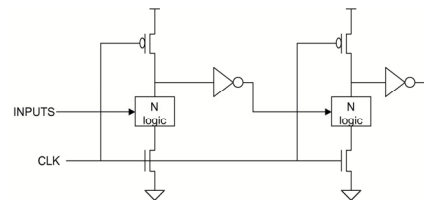
Only 0 → 1 transitions allowed at inputs!

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## Domino Logic

### • Solves cascade problem

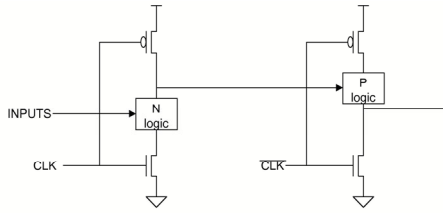


Since the pre-charged output from the first stage is 0, it will never activate the pull-down network in the second stage until the first stage evaluation has completed.

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## NP Domino (Zipper) CMOS



Since the second stage is built from p-logic, the pre-charged output from the first stage will not activate the inputs of the second stage